ase type a pl	lus sign (+) inside	+ this box. FC	ORM PTO/SE	3/08		98706
Substitute f	for form 1449A/P	то		Co.	mplete if Known	201
Oubstitute .	.0, .0			Application Number		- 60
INFORM	ATION DISC	LOSURE		Filing Date	Concurrently Herewith	9,
	ENT BY APP			First Named Inventor	Rama I. Hegde	Ť
OIA LI				Group Art Unit		
(use as mar	ny sheets as nece	essary)		Examiner Name		
Sheet	11	of	2	Attorney Docket Number	SC11697TP	

			U. S	6. PATENT DOCUMENTS		O I A Miles
Examiner Initials*	Cite No. <sup>1</sup>	Number Code <sup>2</sup>	Kind (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
AKS	AA	6,235,594 B1		Merchant et al.	05-22-2001	
AKS	AB	2001/0024387 A1		Raaijmakers et al.	02-27-2001	
AICS	AC	2001/0013629 A1		Bai	08-16-2001	
AICS	AD	5,885,877		Gardner et al.	03-23-1999	
AKS	AE	6,320,244 B1		Alers et al.	11-20-2001	
BKS	AF	6,340,827 B1		Choi et al.	01-22-2002	
AKS	AG	5,153,701		Roy	10-06-1992	
AKI	АН	6,090,686		Brady et al.	07-18-2000	

			FO	REIGN PAT	ENT DOCUMENTS			1 = 5
Examiner	Cite	For	eign Patent Docu	ment	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines,	T°
	No. <sup>1</sup>	Office <sup>3</sup> Code <sup>2</sup>	Number ⁴	Kind (if known)			Where Relevant Passages or Relevant Figures Appear	
	_			(II KIIOWII)				
	<del>  -</del>	<del></del>						<b>†</b>
		-				<del> </del>		<del>                                     </del>
		<del>                                     </del>						<del>                                     </del>
								├
<u> </u>								<del> </del> -
								ļ.—-
								L
	<del> </del>	+						1

Examiner Signature	Asslu	Ummar	Sanhar	Date Considered	3/21	03

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> See Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English Language Translation is attached.

Please type a plus sign (+) inside this box. FORM PTO/SB/08

Substitute for	r form 1449A/PTO			Con	nplete if Known	
				Application Number		
INFORMA	TION DISCLOSU	JRE		Filing Date		
STATEME	NT BY APPLICA	NT		First Named Inventor	Rama I. Hegde	
				Group Art Unit		
(use as many	sheets as necessary	)		Examiner Name		
Sheet	2	of	2	Attorney Docket Number	SC11697TP	

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Alcs	Al	D. Prot et al., "Self-diffusion in α-A1 <sub>2</sub> O <sub>3</sub> IL Oxygen diffusion in 'undoped' single crystals", 1996 Taylor & Francis Ltd., Philosophical Magazine A, 1996, Volume 73, No. 4, pgs 899-917.	
Alcs	AJ	H. Bender et al., "Physical Characterisation of High-k Gate Stacks Deposited on HF-Last Surfaces", IWGI 3002, Tokyo, pgs. 1-7.	
AKS	AK	R.J. Carter et al., "Electrical Characterisation of High-K Materials Prepared by Atomic Layer CVD", IWGI 2001, Tokyo, pgs. 1-6.	
AICS	AL	L. Manchanda et al., "Multi-component high-K gate dielectrics for the silicon industry", Elsevier Science B.V., pgs. 351-359.	
AKS	AM	V.V. Afanas'ev <sup>a.</sup> et al., "Energy barriers between (100)Si and Al <sub>2</sub> O <sub>3</sub> and ZrO <sub>2</sub> -based dielectric stacks: internal electron photoemission measurements", 2001 Elsevier Science B.V. All rights reserved, pgs. 335-339.	
AKS	AN	Massimo Fischetti et al., "IBM Research Report", RC 22092 (99048) June 12, 2001, pgs. 1-25.	
Alcs	AO	D.A. Neumayer et al., "Materials characterization of ZrO <sub>2</sub> -SiO <sub>2</sub> and HfO <sub>2</sub> -SiO <sub>2</sub> binary oxides deposited by chemical solution deposition", 2001 American Institute of Physics, Journal of Applied Physics, Vol. 90, No. 4, August 15, 2001, pgs. 1801-1808.	
AKS	AP	Toyokazu Tambo et al., "Molecular Beam Epitaxy of SrTiO <sub>3</sub> Films on Si(100)-2x1 with SrO Buffer Layer", 1998 Publication Board, Japanese Journal of Applied Physics, Jpn. J. Appl. Phys. Vol. 37 (1998), pgs 4454-4459.	

Examiner Signature	Assu	Unman	Swelvax	Date Considered	3/21	03

EXAMINER. Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered include copy of this form with next communication to applicant

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English Language Translation is attached.